

BCV64B

PNP general-purpose double transistor Rev. 4 — 2 August 2010

Product data sheet

Product profile

1.1 General description

PNP general-purpose double transistor in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number	Package		PNP complement
	NXP	JEITA	
BCV64B	SOT143B	-	BCV63B

1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V and 6 V)
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

- General-purpose switching and amplification
- For use in Schmitt trigger applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _C	collector current		-	-	-100	mA
Transisto	r TR1					
V_{CEO}	collector-emitter voltage	open base	-	-	-30	V
h _{FE}	DC current gain	$V_{CE} = -5 \text{ mV};$ $I_C = -2 \text{ mA}$	220	-	475	
Transisto	r TR2					
V_{CEO}	collector-emitter voltage	open base	-	-	-6	V
h _{FE}	DC current gain	$V_{CE} = -700 \text{ V};$ $I_{C} = -2 \text{ mA}$	<u>[1]</u> 220	-	475	

^[1] Due to matched dies, h_{FE} values for TR2 are the same as for TR1.



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2. Pinning information

Table 3. Pinning

Table 3.	Filling		
Pin	Description	Simplified outline	Graphic symbol
1	collector TR2 and base TR1		
2	collector TR1	4 3 	2 1
3	emitter TR1 and TR2		
4	base TR2	1 2	TR1
			3 4
			006aab230

3. Ordering information

Table 4. Ordering information

Type number	Package	Package			
	Name	Description	Version		
BCV64B	-	plastic surface-mounted package; 4 leads	SOT143B		

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BCV64B	*C6

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current		-	-200	mA
I _B	base current		-	-100	mA
Transistor	r TR1				
V_{CBO}	collector-base voltage	open emitter	-	-30	V
V_{CEO}	collector-emitter voltage	open base	-	-30	V
Transistor	r TR2				
V_{CBO}	collector-base voltage	open emitter	-	-6	V
V_{CEO}	collector-emitter voltage	open base	-	-6	V
Per device	9				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W

^[1] Device mounted on an FR4 PCB.

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7. Characteristics

Table 8. Characteristics

 $T_i = 25$ °C unless otherwise specified.

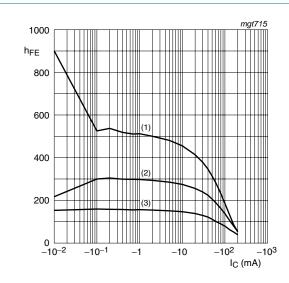
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	sistor						
I _{CBO}	collector-base	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$		-	-	-15	nA
	cut-off current	$V_{CB} = -30 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 \text{ °C}$		-	-	-5	μА
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$		-	-7 5	-300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	[2]	-	-700	-	mV
Transisto	or TR1						
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$		220	-	475	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$		-	-250	-650	mV
V_{BEsat}	base-emitter saturation voltage	$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$	[2]	-	-850	-	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA};$ $V_{CE} = -5 \text{ V}$	[3]	-600	-650	-750	mV
		$I_{C} = -10 \text{ mA};$ $V_{CE} = -5 \text{ V}$	[3]	-	-	-820	mV
f⊤	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	4	-	pF
Transisto	or TR2						
h _{FE}	DC current gain	$V_{CE} = -700 \text{ mV};$ $I_{C} = -2 \text{ mA}$	[1]	220	-	475	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -100 \text{ mA};$ $I_{B} = -5 \text{ mA}$		-	-250	-	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA};$ $V_{CE} = -700 \text{ mV}$	[3]	-	-700	-	mV

^[1] Due to matched dies, h_{FE} values for TR2 are the same as for TR1.

^[2] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[3] V_{BE} decreases by about 2 mV/K with increasing temperature.

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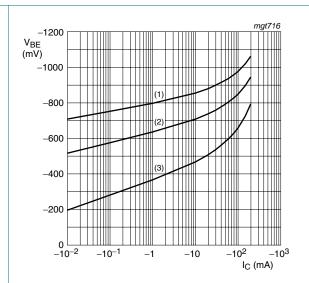
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 1. DC current gain as a function of collector current; typical values



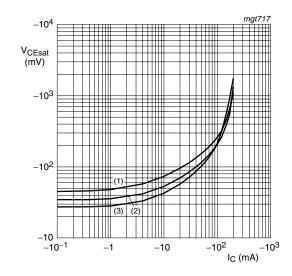
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 2. Base-emitter voltage as a function of collector current; typical values



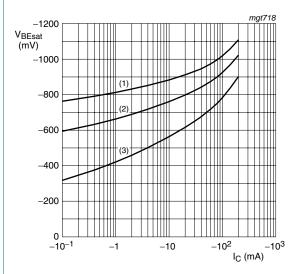
 $I_{\rm C}/I_{\rm B}=20$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

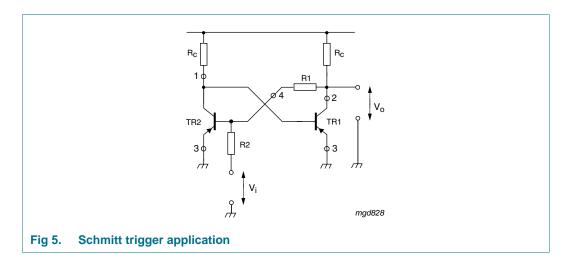
(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 4. Base-emitter saturation voltage as a function of collector current; typical values

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8. Application information



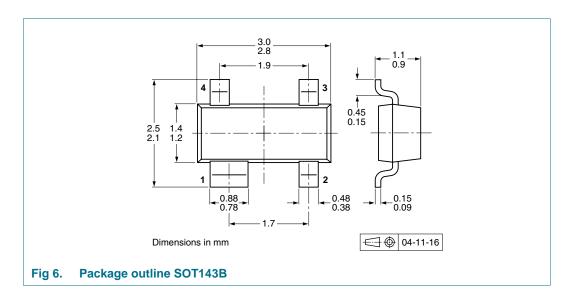
9. Test information

9.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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10. Package outline



11. Packing information

Table 9. Packing methods

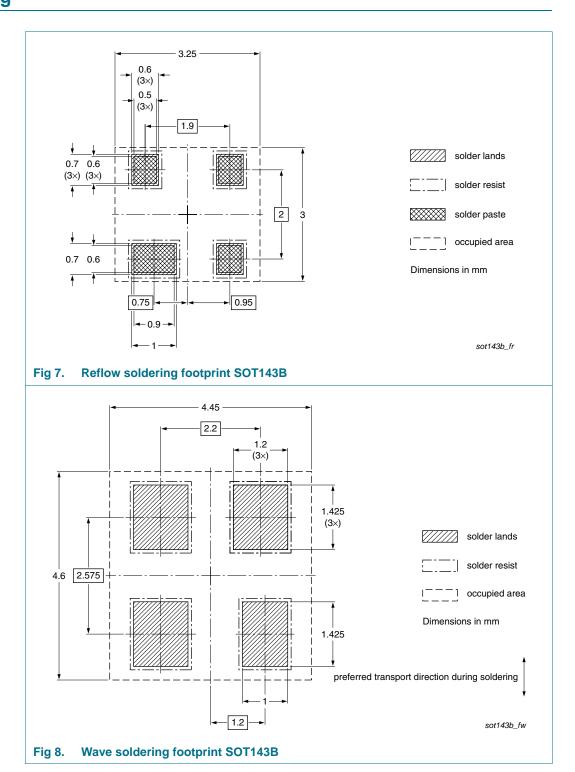
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Packing quantity		ıantity
			3000	10000
BCV64B	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235

^[1] For further information and the availability of packing methods, see Section 15.

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12. Soldering





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13. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BCV64B v.4	20100802	Product data sheet	-	BCV64B_3			
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity			
	 Legal texts 	have been adapted to the n	ew company name whe	ere appropriate.			
	 Section 1 "I 	Product profile": amended.					
	 Section 3 "0 	Ordering information": added	d.				
	 Section 4 "I 	Marking": updated.					
	• <u>Figure 1, 2,</u>	3 and 4: added.					
	 Section 8 "/ 	Application information": add	led.				
	• Section 9 "Test information": added.						
	• Figure 6: superseded by minimized package outline drawing.						
	Section 11	"Packing information": adde	d.				
	• Section 12	"Soldering": added.					
	Section 14	"Legal information": updated	d.				
BCV64B_3	19990521	Product specification	-	BCV64_CNV_2			
BCV64 CNV 2	19970310	Product specification	-	-			

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14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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BCV64B **NXP Semiconductors**

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